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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; Mail Stop 525, 8000 South Federal Way, Boise, ID 83707-0006 (US).

(72) Inventor; and
(75) Inventor/Applicant *(for US only)*: **WELLS, David, H.** [US/US]; 300 Fall Drive, Boise, ID 83706 (US).

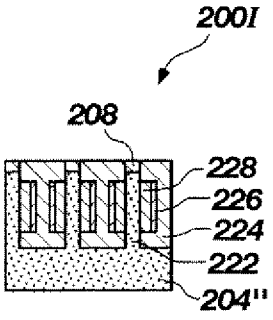
(74) Agents: **WALKOWSKI, Joseph, A.** et al.; Traskbritt, 230 South 500 East, Suite 300, P.O. Box 2550, Salt Lake City, UT 84110-2550 (US).

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(54) Title: METHODS OF ETCHING A PATTERN LAYER TO FORM STAGGERED HEIGHTS THEREIN AND INTERMEDIATE SEMICONDUCTOR DEVICE STRUCTURES



(57) Abstract: A method of forming staggered heights in a pattern layer of an intermediate semiconductor device structure. The method comprises providing an intermediate semiconductor device structure comprising a pattern layer and a first mask layer. forming first openings in the pattern layer, forming spacers adjacent to etched portions of the pattern layer to reduce a width of the first openings, etching the pattern layer to increase a depth of the first openings, and forming second openings in the pattern layer, A method of forming staggered heights in the pattern layer that includes spacers formed on multiple mask layers is also disclosed. Intermediate semiconductor device structures are also disclosed.

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